

Inductor Built-in Negative Output Voltage DC/DC Converters

■GENERAL DESCRIPTION

☆Green Operation Compatible

MYRNP050030W21RA / MYRNP050030B21RA are small coil-integrated negative voltage DC/DC converter IC.

The oscillating frequency is a fast $\dot{2}$.5MHz and the small $2.5 \times 2.0 \times 1.0$ mm package contributes significantly to space saving in PCB area.

Further, integrating the coil together with the DC/DC simplifies the circuit board layout and minimizes potential noise interference. Compared to a charge pump type solution, the switching method of the MYRNP-W/B series maintains a stable output voltage even when the input voltage fluctuates. In addition, this new mini DC/DC can support larger output current than a charge pump solution.

The PWM controlled MYRNP050030W21RA can be selected for applications where low noise is important, and the PWM/PFM automatic switching controlled MYRNP050030B21RA can be selected for applications where high efficiency at light load current and low noise at high load current is important.

The MYRNP-W/B series allows users to select either a PWM control or PWM/PFM automatic switching control method, which are optimum for applications where low noise and high efficiency are important.

Output voltage can be adjusted within the range of -1.2V to -6.0V using externally mounted resistors.





■APPLICATIONS

Negative power supply for Optical transceiver

Negative power supply for AMP

Negative power supply for LCD

Negative power supply for CCD

General purpose Negative power supply

■FEATURES

Output Current : $300 \text{mA @V}_{\text{OUT}}$ =-3.0V, V_{IN} =3.3V(TYP.)

Quiescent Current : 250µA(TYP.)

Control Methods : PWM Control (MYRNP050030W21RA)

PWM/PFM Control (MYRNP050030B21RA)

Oscillation Frequency : 2.5MHz

Protection Function : Current Limit (1.1A TYP.)

Function : Soft Start Time External Adjustment

UVLO

Operating Ambient Temperature : $-40 \sim +105^{\circ}C$

Packages : 2.5 x 2.0 x 1.0mm

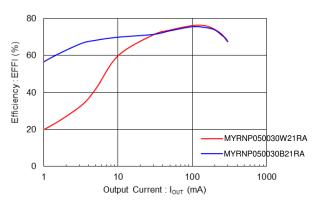
Environmentally Friendly : EU RoHS Compliant, Pb Free

Halogen Free

■TYPICAL APPLICATION CIRCUIT

■TYPICAL PERFORMANCE CHARACTERISTICS

$$\begin{split} & \text{MYRNP050030W21RA/MYRNP050030B21RA} \\ & (V_{\text{\tiny N}} = 3.7V, \, V_{\text{\tiny OUT}} = \text{-}3.3V) \end{split}$$

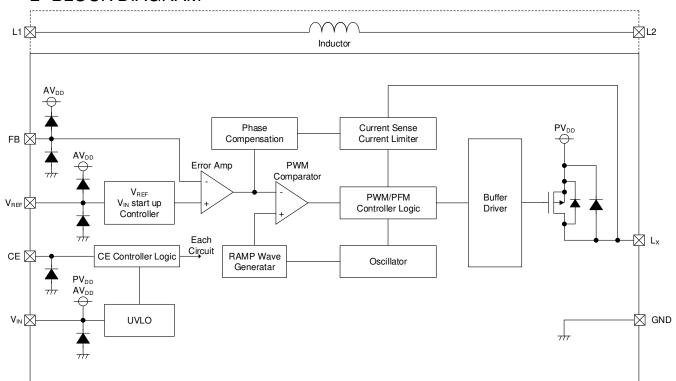


Export Control Code: X0863, Document No: D90DH - 00067



Inductor Built-in Negative Output Voltage DC/DC Converters

BLOCK DIAGRAM

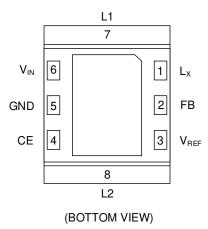


^{*} Diodes inside the circuit are an ESD protection diode and a parasitic diode.



Inductor Built-in Negative Output Voltage DC/DC Converters

■ PIN CONFIGURATION



^{*} The dissipation pad should be solder-plated in recommended mount pattern and metal masking to enhance mounting strength and heat release. If the pad needs to be connected to other pins, it should be connected to the GND (No. 5) pin.

■ PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTIONS
1	Lx	Switching Output
2	FB	Feedback Voltage
3	VREF	Reference Voltage
4	CE	Chip Enable
5	GND	Ground
6	VIN	Power Input
7	L1	Inductor Electrodes
8	L2	Inductor Electrodes

■ FUNCTION

PINNAME	SIGNAL	STATUS
CE -	Н	Operation
	L	Stand-by

^{*} Please do not leave the CE pin open.

■ ABSOLUTE MAXIMUM RATINGS

Ta=25°C

PARAMETER	SYMBOL	RATINGS	UNITS
V _{IN} Pin Voltage	V _{IN}	-0.3 ~ +6.2	V
L _x Pin Voltage	V _{LX}	V _{IN} -13.0 ~ V _{IN} +0.3 or +6.2 (*1)	V
FB Pin Voltage	V _{FB}	-0.3 ~ V _{IN} +0.3 or +6.2 (*1)	V
V _{REF} Pin Current	I _{REF}	-1.0 ~ +1.0 ^(*3)	mA
V _{REF} Pin Voltage	V_{REF}	-0.3 ~ V _{IN} +0.3 or +6.2 (*1)	V
CE Pin Voltage	V _{CE}	-0.3 ~ +6.2	V
Power Dissipation	Pd	1000 (40mm x 40mm Standard board) (*2)	mW
Operating Ambient Temperature	Topr	-40 ~ +105	°C
Storage Temperature	Tstg	-55 ~ +12 5	°C

^{*} All voltages are described based on the GND pin.

^(*1) The maximum value should be either VIN+0.3V or +6.2V in the lowest.

^(°2) The power dissipation figure shown is PCB mounted and is for reference only.

^(*3) Please do not apply voltage to the VREF pin from outside.



Inductor Built-in Negative Output Voltage DC/DC Converters

IELECTRICAL CHARACTERISTICS

MYRNP050030W21RA, MYRNP050030B21RA

Ta=25°C

MYRNP050030W21RA, I	WITHINFUSUUS	DUDZ I HA					=25°C
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS	CIRCUIT
Input Voltage	V _{IN}	-	2.7	-	5.5	V	-
FB Voltage	V _{FB(E)} (*2)	$V_{\text{IN}}=V_{\text{CE}}=3.7V$, The voltage which L_X starts oscillation while V_{FB} is increasing.	0.49	0.50	0.51	V	1
V _{REF} Voltage	V _{REF}	$V_{IN}=V_{CE}=3.7V$	1.56	1.60	1.64	٧	1
UVLO Detection Voltage	V _{UVLOD}	V _{IN} =V _{CE} ,V _{FB} =V _{FB(T)} ×1.025 (*3), Voltage which Lx pin holding "L" level (*1)	1.85	2.10	-	V	1)
UVLO Release Voltage	Vuvlor	V _{IN} =V _{CE} , V _{FB(T)} ×1.025 (*3), Voltage which Lx pin holding "H" level (*1)	-	2.25	2.60	٧	1
UVLO Hysteresis Width	V _{UVLOH}	V _{UVLOH} =V _{UVLOR} - V _{UVLOD}	0.08	0.15	0.25	٧	-
Supply Current	I _{DD}	V _{IN} =V _{CE} =5.5V, V _{FB} =V _{FB(T)} ×0.975 (*3)	215	250	310	μΑ	2
Stand-by Current	I _{STB}	V _{IN} =5.5V, V _{CE} =0V	-	0	0.1	μA	2
PFM Switch Current (MYRNP-B Series)	Ірғм	When connected to external components, I _{OUT} =1mA	-	300	-	mA	3
Soft Start Time	tss	FB Voltage rise up time, $V_{FB=0}V \rightarrow V_{FB(T)} \times 0.95 \ ^{(^{\circ}3)}, \ V_{CE}=0V \rightarrow V_{IN}, \\ I_{OUT}=1 mA, \ CV_{REF}=0.47 uF$	0.5	1.5	2.5	ms	3
Oscillation Frequency	fosc	V _{FB} =V _{FB(T)} ×1.025 (*3)	2.1	2.5	2.9	MHz	1
Maximum ON Time	tonmax	V _{FB} =V _{FB(T)} ×1.025 (*3)	300	350	385	ns	1
Minimum ON Time	tonmin	V _{FB} =V _{FB(T)} ×0.975 (*3)	-	-	0	ns	1
Efficiency	EFFI	When connected to external components, Vout=-3.3V, Iout=100mA	-	75	-	%	3
L _X SW "H" ON Resistance (*4)	R _{LXH}	V _{IN} =5.0V, I _{LX} =100mA	-	0.50	0.65	Ω	4
Lx SW "L" Leakage Current	I _{LEAKL}	$V_{\text{IN}} = 5.5V, \ V_{\text{CE}} = 0V, \ V_{\text{LX}} = 0V$	-	0.01	0.1	μΑ	5
Maximum Current Limit	I _{LIM}	When connected to external components	-	1100	-	mA	1
V _{REF} Voltage Temperature Characteristics	△V _{REF} / (V _{REF} • △topr)	-40°C <u><</u> Topr <u><</u> 105°C	-	±50	-	ppm/℃	1
FB Voltage Temperature Characteristics	△V _{FB} / (V _{FB} • △topr)	-40°C <u><</u> Topr <u><</u> 105°C	-	±50	-	ppm/°C	1
CE "H" Voltage	V _{CEH}	V_{IN} =5.5V, V_{FB} = $V_{\text{FB}(T)}$ ×1.025 (*3), Applied voltage to V_{CE} , voltage changes L_{X} to "H" level (*1)	1.2	-	5.5	V	1
CE "L" Voltage	V _{CEL}	V_{IN} =5.5V, V_{FB} = $V_{\text{FB}(T)}$ ×1.025 (*3), Applied voltage to V_{CE} , voltage changes L_X to "L" level (*1)	GND	-	0.4	V	1
CE "H" Current	Ісен	V _{IN} =V _{CE} =5.5V	-0.1	-	0.1	μA	6
CE "L" Current	I _{CEL}	V _{IN} =5.5V, V _{CE} =0V	-0.1	-	0.1	μΑ	6
FB "H"" Current	I _{FBH}	V _{IN} =V _{CE} =V _{FB} =5.5V	-0.1	-	0.1	μΑ	6
FB "L" Current	I _{FBL}	$V_{IN}=V_{CE}=5.5V, V_{FB}=0V$	-0.1	-	0.1	μΑ	6
Inductance Value	L	Test Frequency=1MHz	-	2.2	-	μΗ	-
Inductor Rated Current	I _{DC}	ΔT=+40°C	-	850	-	mA	-

^{*}Unless otherwise stated, $V_{IN} = V_{CE} = 3.7V$

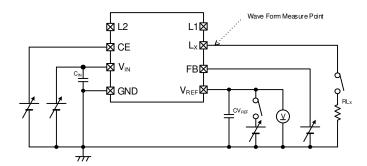
^{(*1) &}quot;H" = $V_{IN} \sim V_{IN} - 1.2V$, "L" = $+0.1V \sim -0.1V$ (*2) $V_{FB(E)}$: Effective FB Voltage, (*3) $V_{FB(T)}$: Setting FB Voltage(0.5V) (*4) ON resistance = $(V_{IN} - V_{LX})$ pin measurement voltage) / 100mA



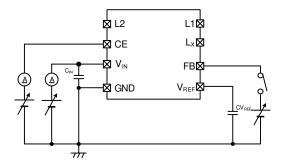
Inductor Built-in Negative Output Voltage DC/DC Converters

■TEST CIRCUITS

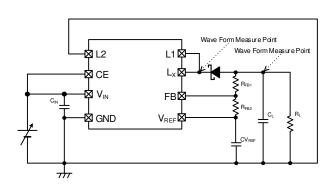
< Test Circuit No. 1 >



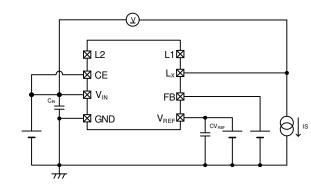
< Test Circuit No.2 >



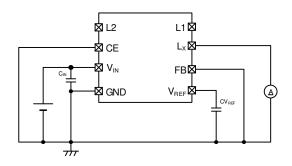
< Test Circuit No. 3 >



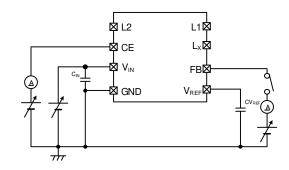
< Test Circuit No.4 >



< Test Circuit No.5 >



< Test Circuit No.6 >

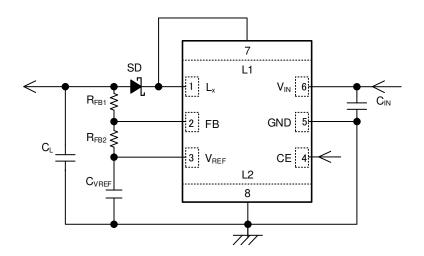




Inductor Built-in Negative Output Voltage DC/DC Converters

■TYPICAL APPLICATION CIRCUIT

EXTERNAL COMPONENTS SELECTION



[Typical example]

	MANUFACTURE	PRODUCT NUMBER	VALUE	Notes
CIN	Murata	GRM188D71A106KA73D	10μF/10V	Ta≦105°C
C⁻	Murata	GRM188D71A106KA73D	10μF/10V	Ta≦105°C
CVREF	Murata	GRM155C71A105KE11	1µF/10V	Ta≦105°C
SD	Nexperia	PMEG2010BELD	1A/20V	=
20	ON Semiconductor	NSR1020MW2	1A/20V	-

^{*}Take capacitance loss, withstand voltage, rated current and other conditions into consideration when selecting components.

When the output capacitor (CL) is large, there is a possibility that the output voltage will be unstable.

<Output voltage (Voutset) setting>

Output voltage can be set by adding an external resistor.

Output voltage is set by the following equation according to RFB1, RFB2, VFB and VREF.

 $V_{OUTSET} = V_{FB} - R_{FB1} / R_{FB2} \times (V_{REF} - V_{FB})$

Please select within $100k\Omega \le R_{FB1} + R_{FB2} \le 500k\Omega$ range.

V _{OUTSET}	R _{FB1}	R _{FB2}
-1.2V	200kΩ	130kΩ
-3.3V	150kΩ	43kΩ
-5.0V	220kΩ	43kΩ

^{*10} μ F ~ 44 μ F output capacitor (C_L) value is recommended.

^{*}If a tantalum or electrolytic capacitor is used for the output capacitor (C_L), ripple voltage will increase, and there is a possibility that operation will become unstable. Test fully using the actual device.

^{*}When Schottky Diodes, which have a large junction capacity are used, there is a possibility that the output voltage will be unstable.



Inductor Built-in Negative Output Voltage DC/DC Converters

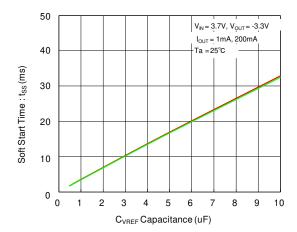
■TYPICAL APPLICATION CIRCUIT

EXTERNAL COMPONENTS SELECTION (Continued)

<Setting soft start time (tss)>

Soft start time is determined by the capacity of the CVREF connected to the VREF terminal.

Please select the capacitance value of C_{VREF} within the range of 0.47μF ~ 10μF referring to the below graph.



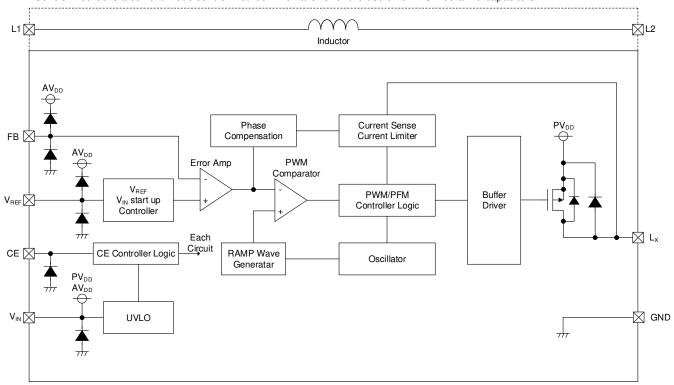


Inductor Built-in Negative Output Voltage DC/DC Converters

■ OPERATIONAL EXPLANATION

This IC consists of a standard voltage reference, error amp, ramp wave circuit, oscillator circuit, PWM comparator, PWM/PFM controller, Pch driver transistor, current sensing circuit, UVLO circuit, VREF startup circuit and etc.

Control method is a current mode control method which allows for the use of low ESR ceramic capacitors.



MYRNP050030W21RA / MYRNP050030B21RA block diagram



Inductor Built-in Negative Output Voltage DC/DC Converters

■ OPERATIONAL EXPLANATION (Continued)

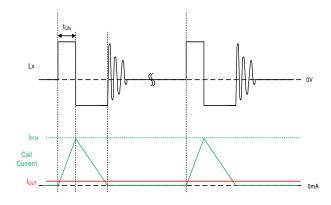
<Normal Operation>

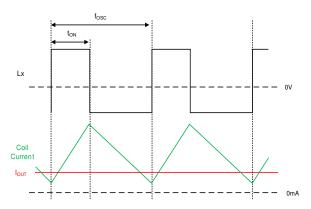
The FB terminal voltage divided by the output voltage is compared with the V_{REF} voltage by the error amp. Phase compensation is applied to the error amp output, which is then forwarded to the PWM comparator. At the PWM comparator the error amp output and ramp wave are compared to determine the ON time during PWM control.

The MYRNP050030W21RA (PWM control) is switched using a constant switching frequency (fosc) independent of the output current. During light load current, the ON time is short, and the IC operates in a non-continuous mode. As the output current increases, the ON time becomes longer, and the IC operates in a continuous mode.

At high load currents, the ON time depends heavily on the input voltage, output voltage, and output current, and the maximum ON time (tonmax) restriction determines the maximum output current that can flow under the conditions of each input voltage and output voltage.

Refer to the typical performance characteristics for the maximum output current under each condition.



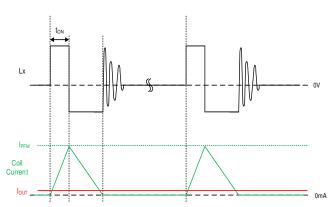


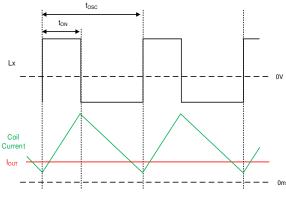
MYRNP050030W21RA: Example of operation at light load current

MYRNP050030W21RA: Example of operation at high load currents

The MYRNP050030B21RA (PWM/PFM automatic switching control) turns ON the Pch driver transistor until the coil current reaches the PFM current (I_{PFM}) and to lower the switching frequency during light load current. This operation reduces loss during light loads to achieve high efficiency from light to high load currents.

As the output current grows larger, the switching frequency increases proportional to the output current, and when the switching frequency reaches the fosc to switch from PFM control to PWM control the switching frequency is fixed.





MYRNP050030B21RA: Example of operation at light load current

MYRNP050030B21RA: Example of operation at high load currents

Further, the phase compensation circuit optimizes the error amp frequency characteristics and is used to phase compensate the Pch driver transistor current feedback signal. This achieves output voltage stability even when low ESR capacitors, such as ceramic capacitors are used.



Inductor Built-in Negative Output Voltage DC/DC Converters

■ OPERATIONAL EXPLANATION (Continued)

<CE Function>

When a "H" voltage (V_{CEH}) is input to the CE terminal, it operates normally after the output voltage is started by the soft start function.

When a "L" voltage (V_{CEL}) is input to the CE terminal, it goes to the stand-by state, the quiescent current is suppressed to the stand-by current I_{STB} (TYP.0 µA) level and the Pch driver transistor turns OFF.

<UVLO Function>

When the V_{IN} terminal voltage drops below the UVLO detect voltage level (V_{UVLOD}), the UVLO function operates and turns off the Pch driver transistor to prevent any erroneous pulse output due to possible unstable action of the internal circuit.

When the V_{IN} terminal voltage increases above the UVLO release voltage level (V_{UVLOR}), the UVLO function is released. After the UVLO function is released, the soft start function starts the output voltage and the IC operates normally.

The UVLO function operates even if the VIN terminal momentarily drops below the UVLO detect voltage.

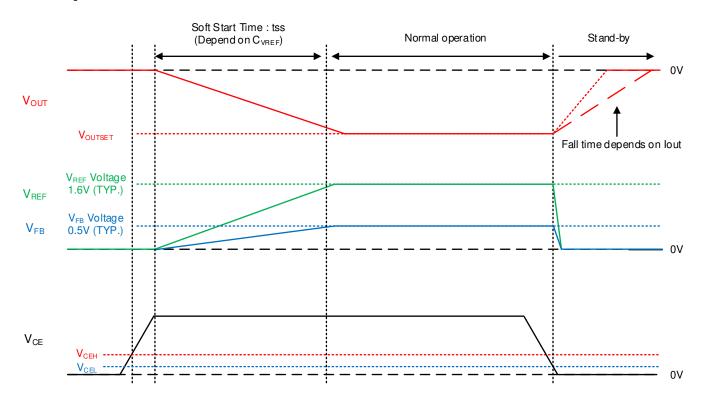
In addition, whilst the UVLO function is in operation, rather than being in a stand-by state, the IC is in a switching operation stopped state, so the internal circuit is still operating.

<Soft Start Function>

This gently starts up the output voltage when the IC starts up and the UVLO function is released to suppress the inrush current. The VREF startup circuit operates after the "H" voltage (VCEH) is input to the CE terminal and after the UVLO function is released. The VREF startup circuit charges the CVREF with current and can gently raise the VREF voltage and FB voltage. In response to this, the output voltage is lowered proportionally to the increase in the VREF voltage and FB voltage. This action makes it possible to prevent input current inrush and to smoothly lower the output voltage.

The output voltage startup time (soft start time) is determined by the capacity of the CVREF connected to the VREF terminal.

In the stand-by state and during the UVLO function operation, the charge accumulated in the C_{VREF} is discharged and the V_{REF} voltage is made to be 0V.





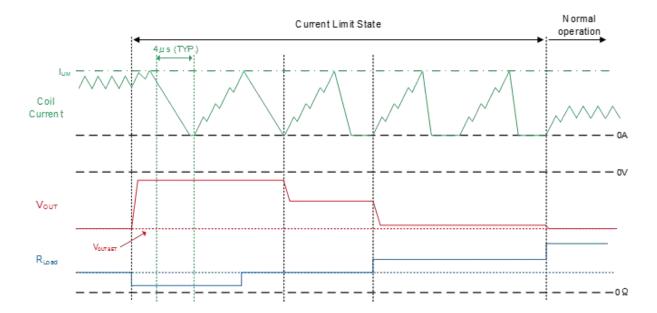
Inductor Built-in Negative Output Voltage DC/DC Converters

■ OPERATIONAL EXPLANATION (Continued)

<Current Limit Function>

The current limit circuit monitors the current flowing to the Pch driver transistor to restrict overcurrent. The current limit function operates as follows.

- 1) The current flowing to the Pch driver transistor is increased, and when the current limit value of ILIM=1100mA (TYP.) is reached, the current limit state is entered and the Pch driver transistor is turned OFF.
- 2) The Pch driver transistor is turned OFF for a period of 4µs (TYP.), and the coil current is greatly decreased. During this time, lowering the coil current that has reached the current limit lowers the input current and output current while the current is restricted.
- 3) Other switching operations are performed, and when the output voltage is a load resistance that does not reach the set voltage, the coil current increases and the current limit function operates again.
- 4) Operations 1) to 3) are repeated during the current limit state period.
- 5) When the load resistance increases much more than the load resistance during current limit detection, the current limit state is released and the IC automatically returns to normal operation.





Inductor Built-in Negative Output Voltage DC/DC Converters

■NOTE ON USE

- 1) For temporary, transitional voltage drop or voltage rising phenomenon, the IC is liable to malfunction should the ratings be exceeded.
- 2) Switching regulators like this DC/DC converter generate spike noise and ripple voltage. This greatly affects the surrounding components (Schottky diodes, capacitors, peripheral component circuit board layout etc.). When making a design, please be sure to sufficiently check this in an actual device.
- 3) The DC/DC converter characteristics greatly depend not only on the characteristics of this IC but also on those of externally connected components, so refer to EXTERNAL COMPONENTS SELECTION and the specifications of each component and be careful when selecting the components. Be especially careful of the characteristics of the capacitor used for the load capacity C_L and use a capacitor with B characteristics (JIS Standard) or an X7R/X5R (EIA Standard) ceramic capacitor.
- 4) The maximum output current of this IC is determined by the current limit value and the maximum ON time restrictions, and this depends greatly on the input voltage and output voltage. Further, when the input voltage is low and during low temperature, there is a possibility that the maximum ON time decreases and the maximum output current drops. For the maximum output current, please refer to the typical performance characteristics of "Maximum Output Current vs. Output Voltage."
- 5) With MYRNP050030W21RA, there is a possibility that the switching frequency will decline when the input voltage is high and the load current is light.
- 6) When Schottky Diodes, which have a large junction capacity, are used or when the CL output capacity is large, there is a possibility that the output voltage will be unstable.
- 7) When there is steep output current fluctuation, there could be a large drop in the output voltage that can cause the duty to increase which in turn triggers the operation of the current limit function.
- 8) If the IC is started under a condition where the output current is large, there is a possibility that the inrush current will increase and the current limit function may operate.
- 9) When the input voltage is lowered below the UVLO detect voltage level for a short time, there are times when it is not possible to discharge the CVREF charge. When the input voltage is started again in this state, the shortening of the soft start time at startup could trigger the current limit function.
- 10) Under the condition where the input voltage is close to 1V, there is a possibility that the UVLO function will not operate.
- 11) Murata places an importance on improving our products and their reliability. We request that users incorporate fail-safe designs and post-aging protection treatment when using Murata products in their systems.
- 12) The proper position of mounting is based on the coil terminal

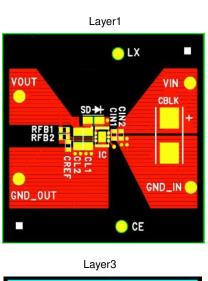


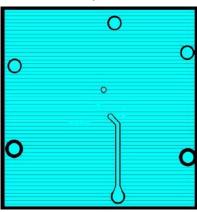
Inductor Built-in Negative Output Voltage DC/DC Converters

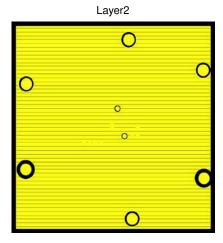
■NOTE ON USE (Continued)

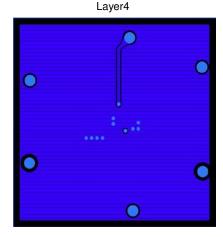
- 13) Note on board layout
 - 1. In order to stabilize V_{IN} voltage level, we recommend that a by-pass capacitor (C_{IN}) be connected as close as possible to the V_{IN} & GND pins.
 - 2. Please mount each external component as close to the IC as possible.
 - 3. Wire external components as close to the IC as possible and use thick, short connecting traces to reduce the circuit impedance.
 - 4. Make sure that the PCB GND traces are as thick as possible, as variations in ground potential caused by high ground currents at the time of switching may result in instability of the IC.
 - This series' internal driver transistors bring on heat because of the output current and ON resistance of Pch driver transistors.
 - 6. As precautions on mounting, please set the mounting position accuracy within 0.05 mm.

Recommended Pattern Layout









- 14) Appearance (Coil)
- Coils are compliant with general surface mount type chip coil (inductor) specifications and may have scratches, flux contamination and the like.

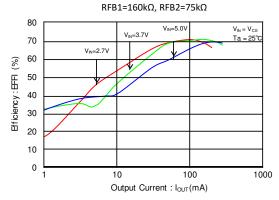


Inductor Built-in Negative Output Voltage DC/DC Converters

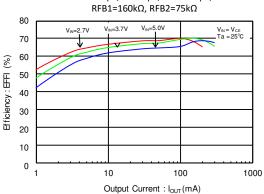
■TYPICAL PERFORMANCE CHARACTERISTICS

(1) Efficiency vs. Output Currrent

MYRNP050030W21RA V_{OUT} = -1.8V CIN=10μF, CL=10μF, CVREF=1μF,

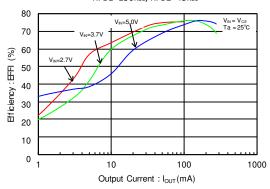


MYRNP050030B21RA V_{OUT} =-1.8V CIN=10μF, CL=10μF, CVREF=1μF,



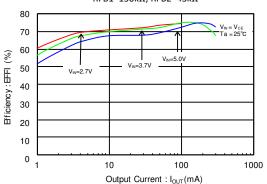
MYRNP050030W21RA $V_{OUT} = -3.3V$

CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω



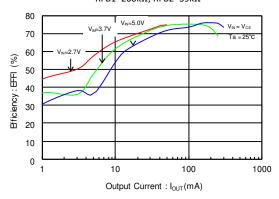
MYRNP050030B21RA V_{OUT} =-3.3V

CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω



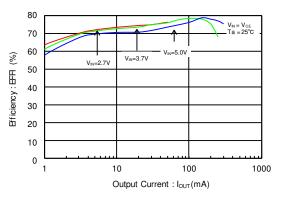
MYRNP050030W21RA $V_{OUT} = -5.0V$

CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=200k Ω , RFB2=39k Ω



$MYRNP050030B21RA \ V_{OUT} = -5.0V$

CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=200k Ω , RFB2=39k Ω

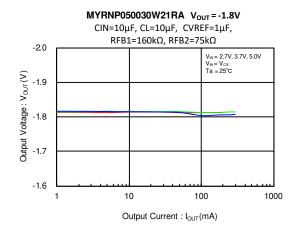


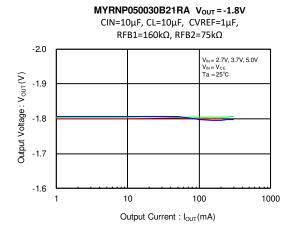


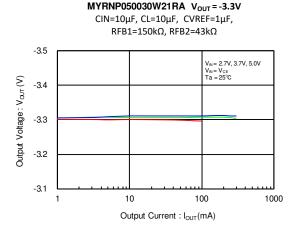
Inductor Built-in Negative Output Voltage DC/DC Converters

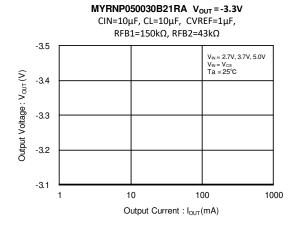
■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

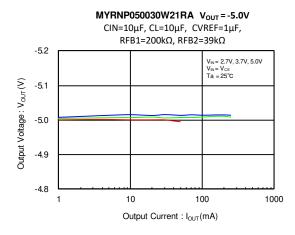
(2) Output Voltage vs. Output Current

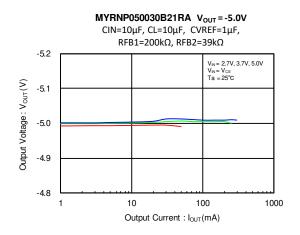










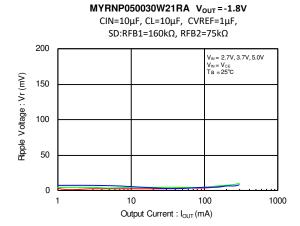


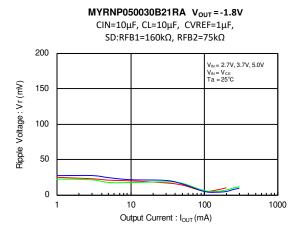


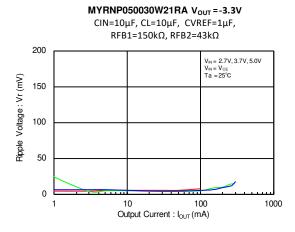
Inductor Built-in Negative Output Voltage DC/DC Converters

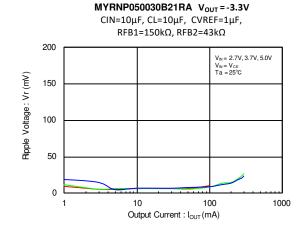
■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

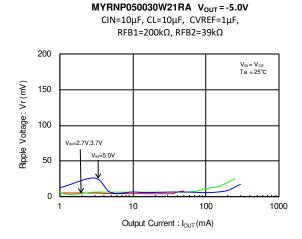
(3) Ripple Voltage vs. Output Current

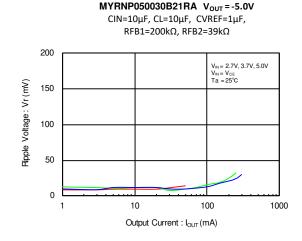










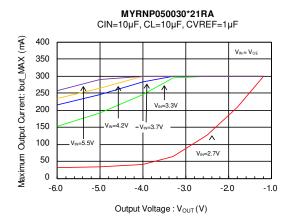




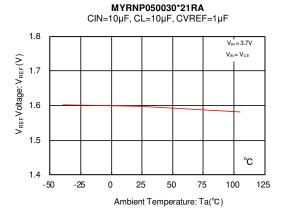
Inductor Built-in Negative Output Voltage DC/DC Converters

■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

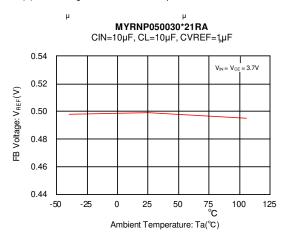
(4) Maximum Output Current vs. Output Voltage



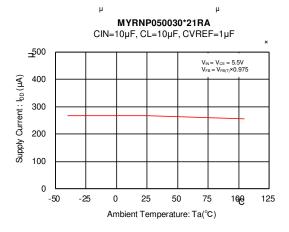
(5) V_{REF} Voltage vs. Ambient Temperature



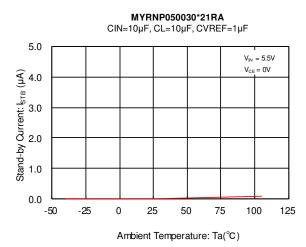
(6) FB Voltage vs. Ambient Temperature



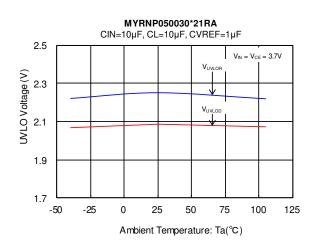
(7) Supply Current vs. Ambient Temperature



(8) Stand-by Current vs. Ambient Temperature



(9) UVLO Voltage vs. Ambient Temperature



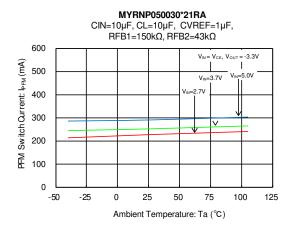


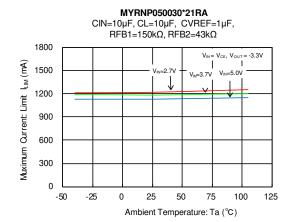
Inductor Built-in Negative Output Voltage DC/DC Converters

■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

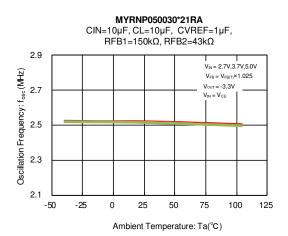
(10) PFM Switch Current vs. Ambient Temperature

(11) Maximum Current Limit vs. Ambient Temperature

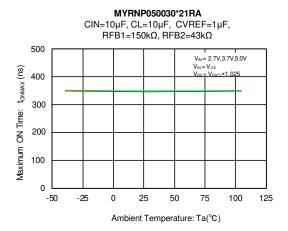




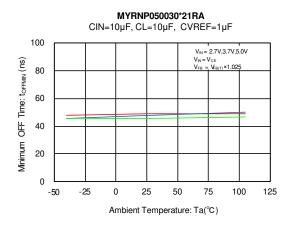
(12) Oscillation Frequency vs. Ambient Temperature



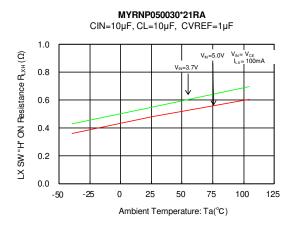
(13) Maximum ON Time vs. Ambient Temperature



(14) Minimum OFF Time vs. Ambient Temperature



(15) Lx SW "H" ON Resistance vs. Ambient Temperature



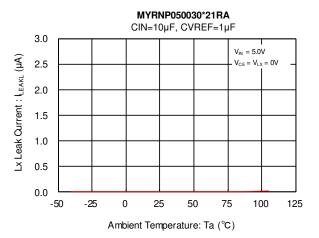


Inductor Built-in Negative Output Voltage DC/DC Converters

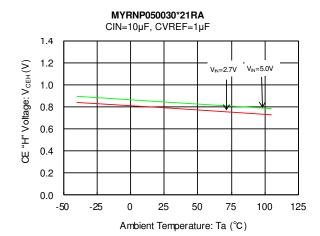
■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

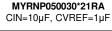
(16) Lx SW "L" Leakage Current vs. Ambient Temperature

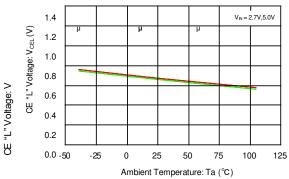
(17) CE "H" Voltage vs. Ambient Temperature











°C

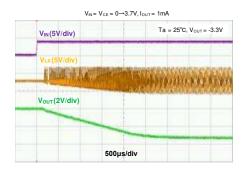


Inductor Built-in Negative Output Voltage DC/DC Converters

■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

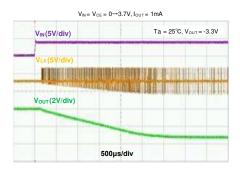
(19) Rising Output Voltage

MYRNP050030W21RA



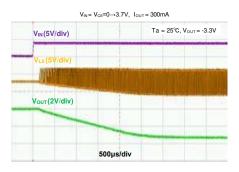
CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω

MYRNP050030B21RA



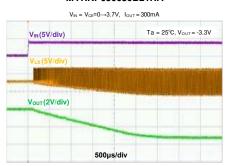
CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω

MYRNP050030W21RA



CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω

MYRNP050030B21RA



CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω

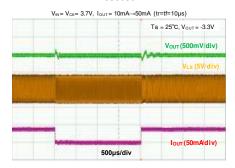


Inductor Built-in Negative Output Voltage DC/DC Converters

■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

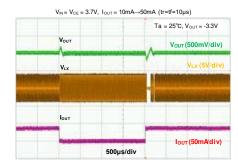
(20) Load Transient Response

MYRNP050030W21RA



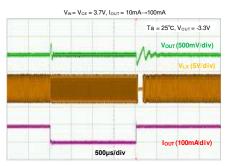
CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω

MYRNP050030B21RA



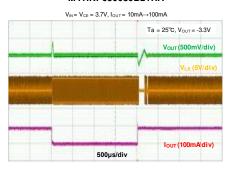
CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω

MYRNP050030W21RA



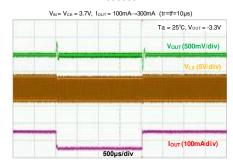
CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω

MYRNP050030B21RA



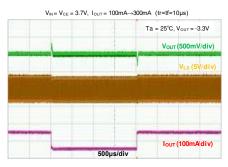
CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω

MYRNP050030W21RA



CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω

MYRNP050030B21RA



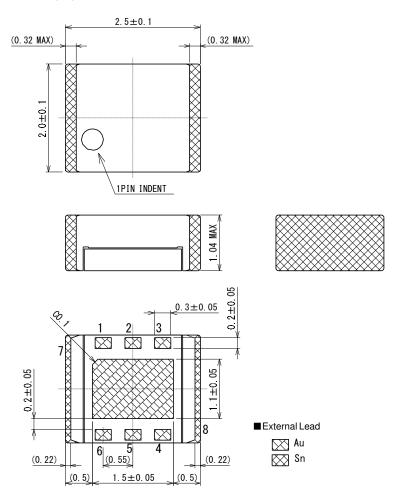
CIN=10 μ F, CL=10 μ F, CVREF=1 μ F, RFB1=150k Ω , RFB2=43k Ω



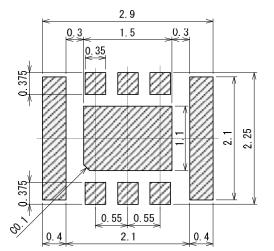
Inductor Built-in Negative Output Voltage DC/DC Converters

■ PACKAGING INFORMATION

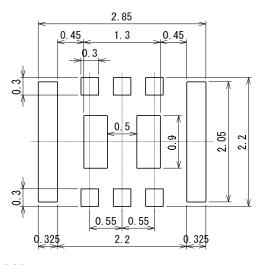
● Packaging (2.0mm × 2.5mm, h=1.0mm)



● Reference Pattern Layout (unit:mm)



● Reference Metal Mask Design (unit:mm)



^{*}Implementation is recommended within accuracy 0.05mm



Inductor Built-in Negative Output Voltage DC/DC Converters

■ PACKAGING INFORMATION

Power Dissipation

Power dissipation data for the package is shown in this page.

The value of power dissipation varies with the mount board conditions.

Please use this data as one of reference data taken in the described condition.

1. Measurement Condition (Reference data)

Condition: Mount on a board Ambient: Natural convection Soldering: Lead (Pb) free

Board Dimensions: 40 x 40 mm (1600mm2 in one side)

Copper (Cu) traces occupy 50% of the board area

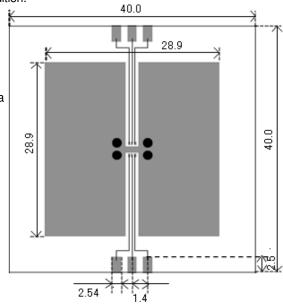
in top and back faces Package heat-sink

is tied to the copper traces.

Material: Glass Epoxy (FR-4)

Thickness: 1.6 mm

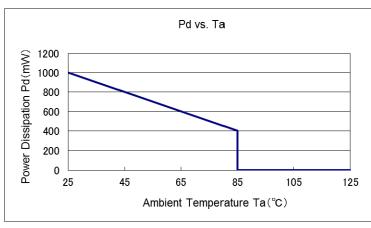
Through-hole: 4 x 0.8 Diameter



Evaluation Board (Unit:mm)

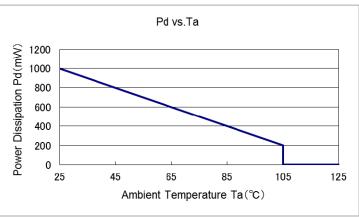
2. Power Dissipation vs. Ambient Temperature(85°C) Board Mount (Tjmax=125°C)

Ambient	Power	Thermal
Temperature	Dissipation	Resistance
(°C)	Pd (mW)	(°C/W)
25	1000	100.00
85	400	100.00



3. Power Dissipation vs. Ambient Temperature(105°C)

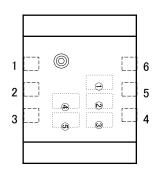
Ambient	Power	Thermal
Temperature	Dissipation	Resistance
(°C)	Pd (mW)	(°C/W)
25	1000	100.00
105	200	100.00





Inductor Built-in Negative Output Voltage DC/DC Converters

■MARKING RULE



① Represents products series

MARK	PRODUCTSERIES
N	MYRNP050030W21RA
Р	MYRNP050030B21RA

② FB voltage

MARK	FB VOLTAGE (V)
0	0.5

③ Represents integer of Oscillation frequency

2 2.5MHz		MARK	OSCILLATION FREQUENCY
	ĺ	2	2.5MHz

4, 5 represents production lot number 01~09、0A~0Z、11~9Z、A1~A9、AA~AZ、B1~ZZ in order. (G, I, J, O, Q, W excluded)

Note: No character inversion used.



Inductor Built-in Negative Output Voltage DC/DC Converters

- 1. The product and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date.
- 2. The information in this datasheet is intended to illustrate the operation and characteristics of our products. We neither make warranties or representations with respect to the accuracy or completeness of the information contained in this datasheet nor grant any license to any intellectual property rights of ours or any third party concerning with the information in this datasheet.
- Applicable export control laws and regulations should be complied and the procedures required
 by such laws and regulations should also be followed, when the product or any information
 contained in this datasheet is exported.
- 4. The product is neither intended nor warranted for use in equipment of systems which require extremely high levels of quality and/or reliability and/or a malfunction or failure which may cause loss of human life, bodily injury, serious property damage including but not limited to devices or equipment used in 1) nuclear facilities, 2) aerospace industry, 3) medical facilities, 4) automobile industry and other transportation industry and 5) safety devices and safety equipment to control combustions and explosions. Do not use the product for the above use unless agreed by us in writing in advance.
- 5. Although we make continuous efforts to improve the quality and reliability of our products; nevertheless Semiconductors are likely to fail with a certain probability. So in order to prevent personal injury and/or property damage resulting from such failure, customers are required to incorporate adequate safety measures in their designs, such as system fail safes, redundancy and fire prevention features.
- 6. Our products are not designed to be Radiation-resistant.
- 7. Please use the product listed in this datasheet within the specified ranges.
- 8. We assume no responsibility for damage or loss due to abnormal use.

Murata Manufacturing Co., Ltd.